

Silicon Diode

NSB8MT

1000V / 8A

DATASHEET

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OEM – General Semiconductor

Source: General Semiconductor Databook 1998

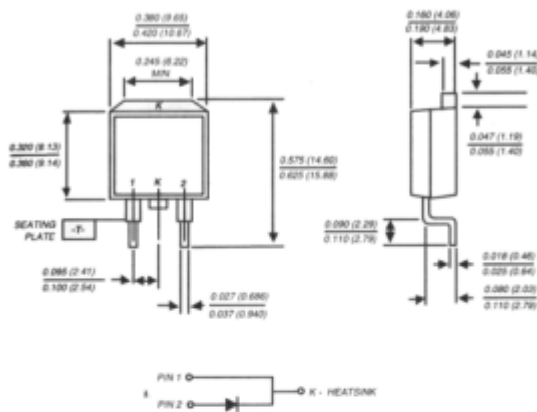
NEW PRODUCT NEW PRODUCT NEW PRODUCT

NSB8AT THRU NSB8MT

GLASS PASSIVATED GENERAL PURPOSE PLASTIC RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 8.0 Amperes

TO-263AA



Dimensions in inches and (millimeters)

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- High forward current capability
- High surge current capability
- Low forward voltage drop
- Glass passivated chip junction
- High temperature soldering in accordance with CECC 802 / Reflow guaranteed



MECHANICAL DATA

Case: JEDEC TO-263AA molded plastic body
Terminals: Plated leads solderable per MIL-STD-750, Method 2026
Polarity: As marked
Mounting Position: Any
Weight: 0.08 ounce, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	NSB8 AT	NSB8 BT	NSB8 DT	NSB8 GT	NSB8 JT	NSB8 KT	NSB8 MT	UNITS
Maximum repetitive peak reverse voltage	VRRM	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	VRMS	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current at TC=100°C	I(AV)	8.0							Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	175.0							Amps
Maximum instantaneous forward voltage at 8.0A	VF	1.1							Volts
Maximum DC reverse current at rated DC blocking voltage	IR	10.0 100.0							µA
Typical junction capacitance (NOTE 1)	CJ	55.0							pF
Typical thermal resistance (NOTE 2)	RθJC	3.0							°C/W
Operating junction and storage temperature range	TJ, TSTG	-55 to +150							°C

NOTES:

- (1) Measured at 1.0 MHz and applied reversed voltage of 4.0 Volts
- (2) Thermal resistance from junction to case mounted on heatsink

RATINGS AND CHARACTERISTIC CURVES NSB8AT THRU NSB8MT

